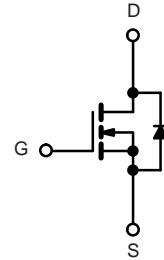
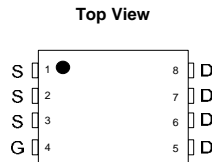
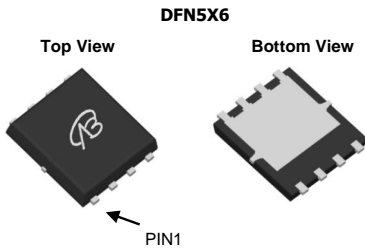


NTMFS0D5N04XL-VB Datasheet
N-Channel 40V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a
40	0.0008 at V _{GS} = 10 V	250
	0.0009 at V _{GS} = 7.5 V	235

FEATURES

- 175 °C Junction Temperature
- SGT technology Power MOSFET
- Material categorization:



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 25 °C	I _D	250	A
	T _C = 100 °C		150 ^a	
Pulsed Drain Current		I _{DM}	750	
Continuous Source Current (Diode Conduction)		I _S	250 ^a	
Avalanche Current		I _{AS}	125	
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	134	mJ
Maximum Power Dissipation	T _C = 25 °C	P _D	136	W
	T _A = 25 °C		3 ^b , 8.3 ^{b, c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 sec	R _{thJA}	15	18	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R _{thJC}	0.85	1.1	

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t ≤ 10 s.

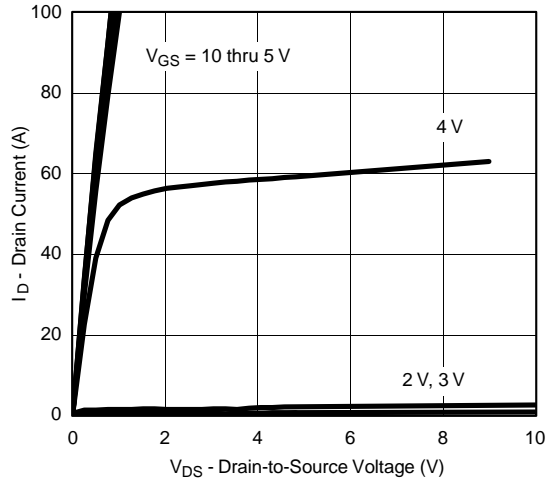
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	40			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.5		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0 V			1	μA
		V _{DS} = 30V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 30V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	60			A
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 40 A		0.0008		Ω
		V _{GS} = 10 V, I _D = 30 A, T _J = 125 °C		0.0012		
		V _{GS} = 10 V, I _D = 30 A, T _J = 175 °C		0.0020		
		V _{GS} = 7.5 V, I _D = 30 A		0.0009		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 20 A		60		S
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 40 V, f = 1 MHz		8800		pF
Output Capacitance	C _{oss}			470		
Reverse Transfer Capacitance	C _{rss}			225		
Total Gate Charge ^c	Q _g	V _{DS} = 40 V, V _{GS} = 10 V, I _D = 50 A		96	70	nC
Gate-Source Charge ^c	Q _{gs}			17		
Gate-Drain Charge ^c	Q _{gd}			15		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 40 V, R _L = 0.6 Ω I _D ≅ 50 A, V _{GEN} = 10 V, R _g = 2.5 Ω		20	23	ns
Rise Time ^c	t _r			15	25	
Turn-Off Delay Time ^c	t _{d(off)}			35	50	
Fall Time ^c	t _f			20	30	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)						
Pulsed Current	I _{SM}				750	A
Diode Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		1	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		4	135	ns

Notes:

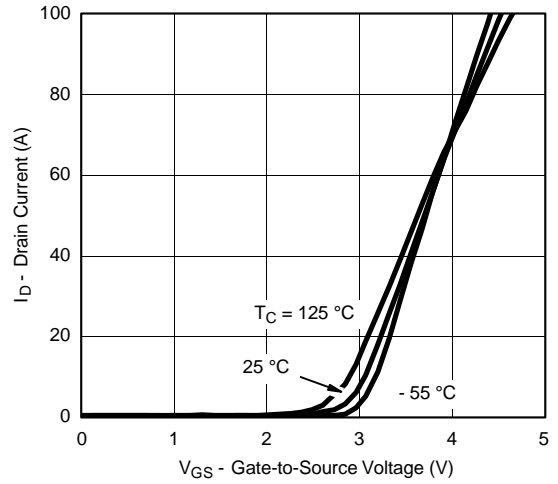
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

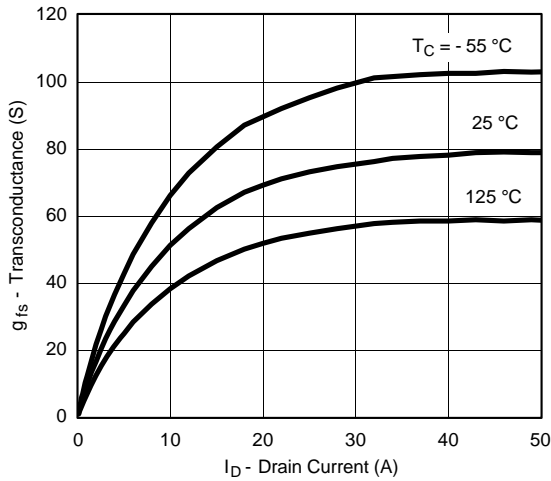
TYPICAL CHARACTERISTICS (25 °C unless noted)



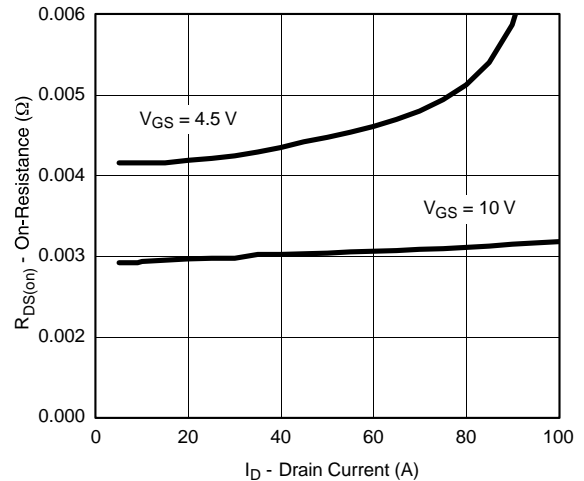
Output Characteristics



Transfer Characteristics



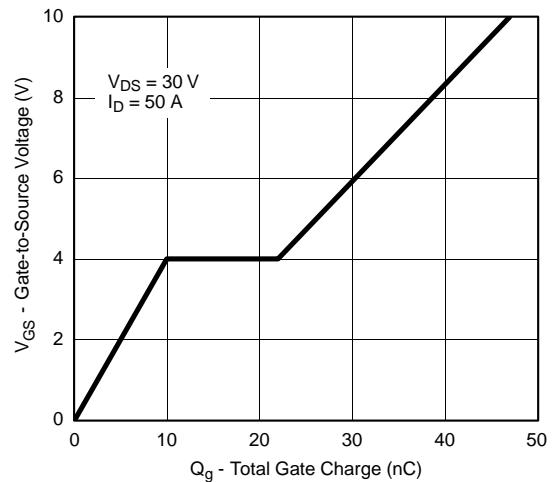
Transconductance



On-Resistance vs. Drain Current

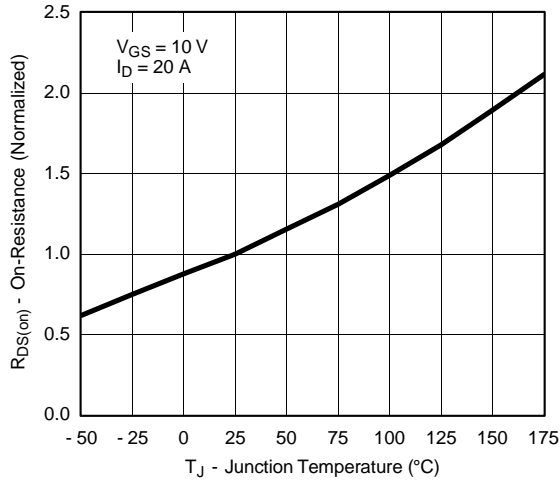


Capacitance

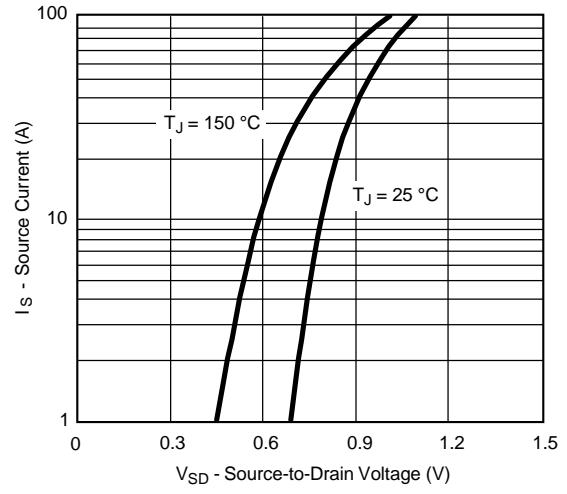


Gate Charge

TYPICAL CHARACTERISTICS (25 °C unless noted)



On-Resistance vs. Junction Temperature

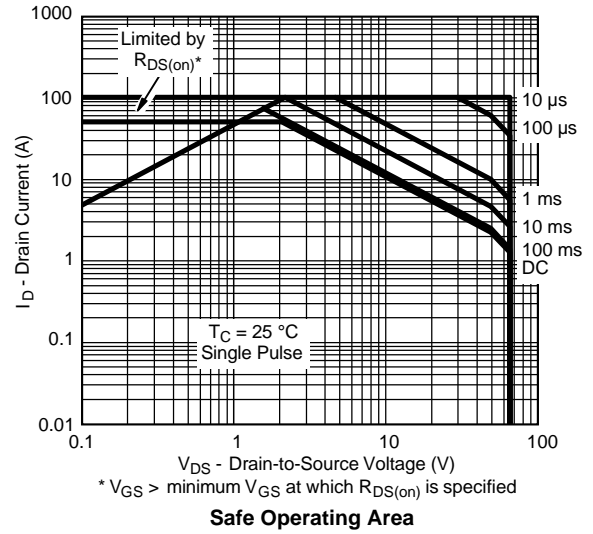


Source-Drain Diode Forward Voltage

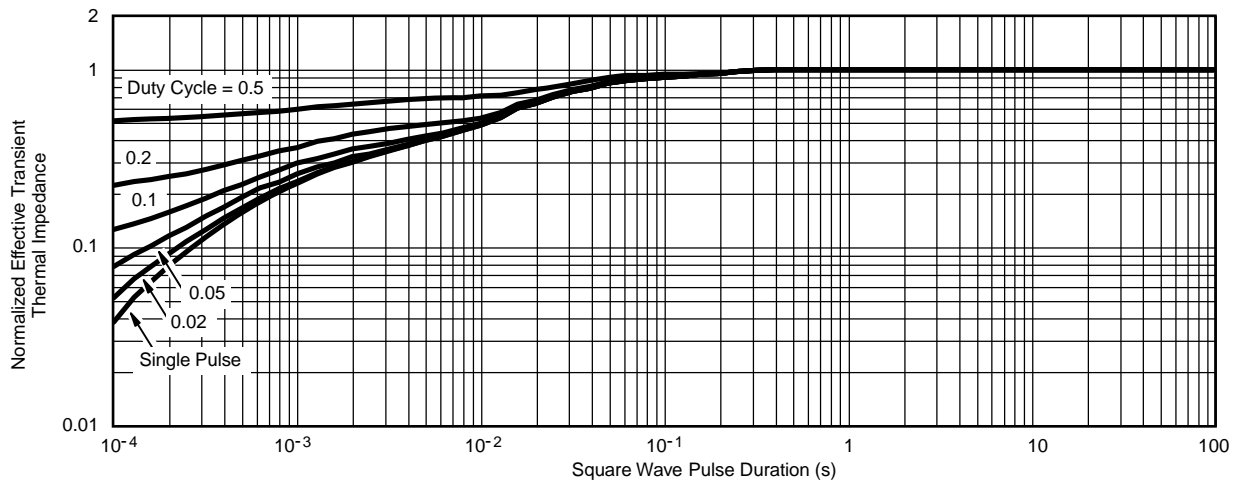
THERMAL RATINGS



Maximum Drain Current vs. Ambient Temperature

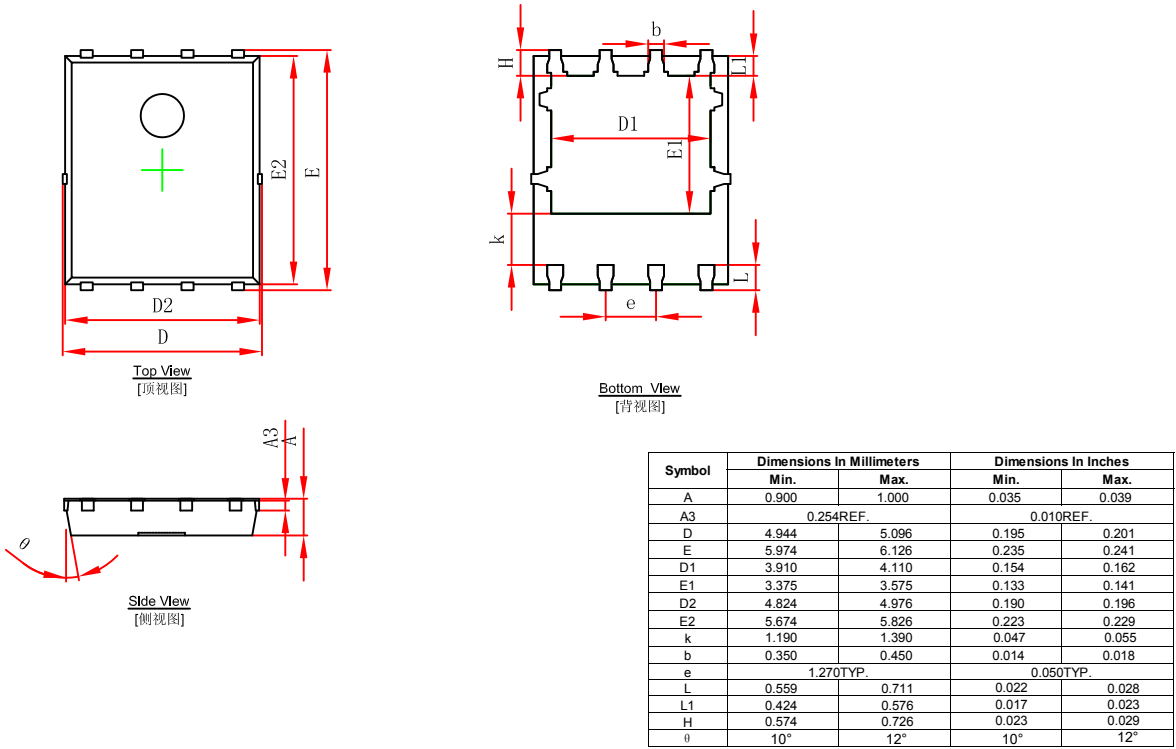


Safe Operating Area

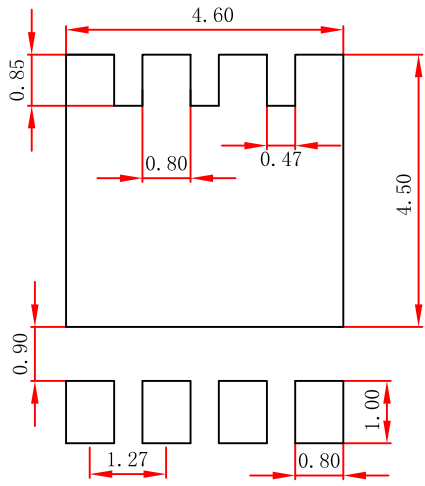


Normalized Thermal Transient Impedance, Junction-to-Case

PDFNWB5x6-8L Package Outline Dimensions



PDFNWB5x6-8L Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ±0.05mm.
 3. The pad layout is for reference purposes only.

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